



Product Standard
MOS FET
MTM78E2B0LBF

MTM78E2B0LBF
Gate Resistor installed Dual N-Channel MOS Type

For lithium-ion secondary battery protection circuit

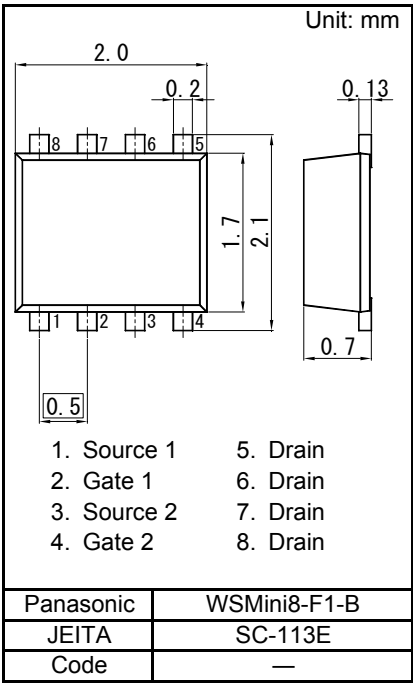
■ Features

- Low drain-source On-state Resistance
RDS(on) typ. = 21.5 mΩ (VGS = 4.0 V)
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 5A

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit
FET1	Drain-source Voltage	VDS	20	V
	Gate-source Voltage	VGS	±12	V
FET2	Drain current	ID	4.0	A
	Peak drain current *1	IDp	40	A
	Total power dissipation	PD1 *2	700	mW
		PD2 *3	150	
Overall	Channel temperature	Tch	150	°C
	Operating ambient temperature	Topr	-40 to +85	°C
	Storage temperature	Tstg	-55 to +150	°C

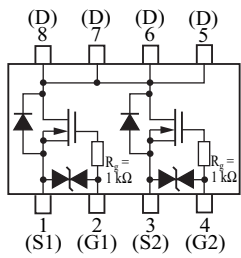
Note) *1 t = 10 μs, Duty Cycle < 1 %

Ceramic substrate (70 × 70 × t 1.0 mm)

*2 Dual operating

*3 Stand-alone (without the substrate)

Internal Connection



Pin Name

- | | |
|-------------|----------|
| 1. Source 1 | 5. Drain |
| 2. Gate 1 | 6. Drain |
| 3. Source 2 | 7. Drain |
| 4. Gate 2 | 8. Drain |



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■ Electrical Characteristics Ta = 25°C ± 3°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	VDSS	ID = 1.0 mA, VGS = 0	20			V
Drain-source cutoff current	IDSS	VDS = 20 V, VGS = 0			1.0	μA
Gate-source cutoff current	IGSS	VGS = ±12 V, VDS = 0			±10	μA
Gate threshold voltage	Vth	ID = 1.0 mA, VDS = 10 V	0.40	0.85	1.30	V
Drain-source ON resistance	RDS(ON)1	ID = 2.0 A, VGS = 4.0 V		21.5	25.0	mΩ
	RDS(ON)2	ID = 1.5 A, VGS = 3.0 V		26.0	30.0	mΩ
	RDS(ON)3	ID = 1.0 A, VGS = 2.5 V		30.0	36.0	mΩ
Forward transfer admittance	Yfs	ID = 1.0 A, VDS = 10 V	1.0			S
Short-circuit input capacitance (Common source)	Ciss	VDS = 10 V, VGS = 0, f = 1 MHz		1100		pF
Short-circuit output capacitance (Common source)	Coss			75		pF
Reverse transfer capacitance (Common source)	Crss			70		pF
Turn-on delay time ^{*1, *2}	td(on)	VDD = 10 V, VGS = 4 V, ID = 1.0 A, RL = 10 Ω		0.2		μs
Rise time ^{*1, *2}	tr			0.5		μs
Turn-off delay time ^{*1, *2}	td(off)			2.0		μs
Fall time ^{*1, *2}	tf			1.5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

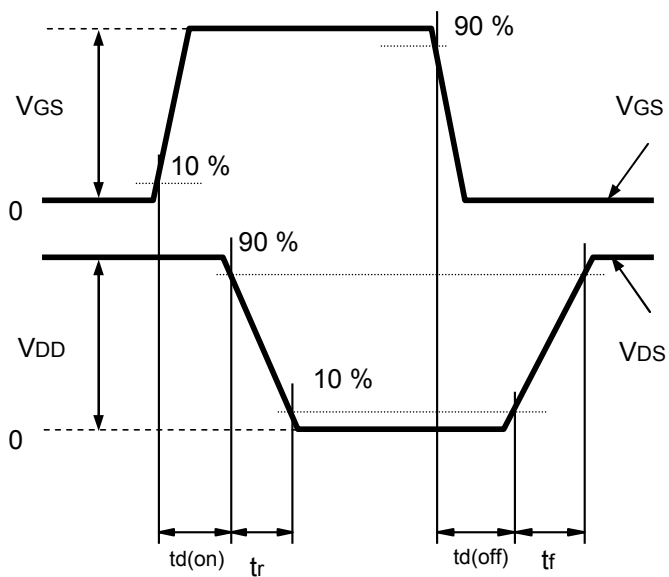
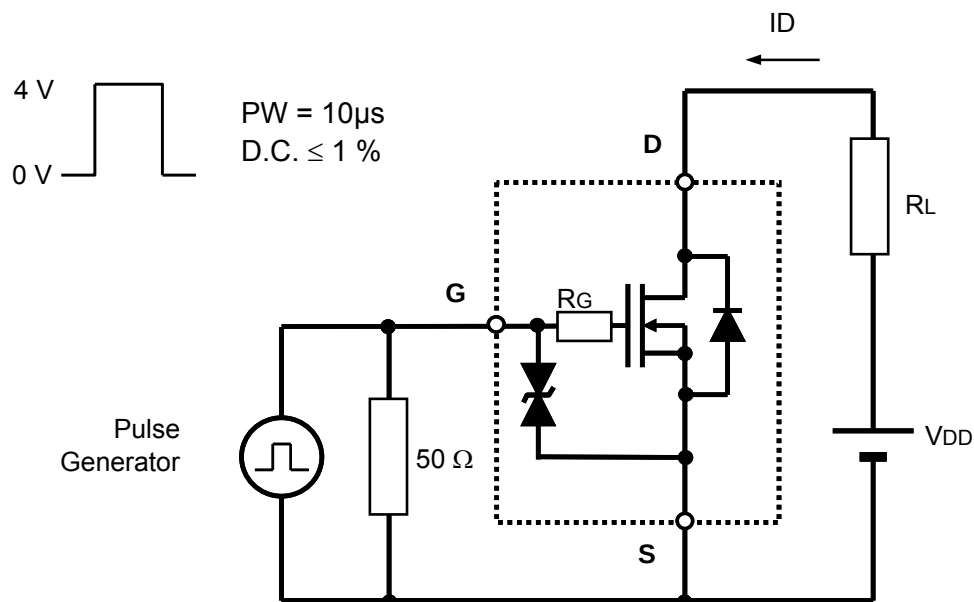
2. *1 t = 10 μs, Duty Cycle < 1 %

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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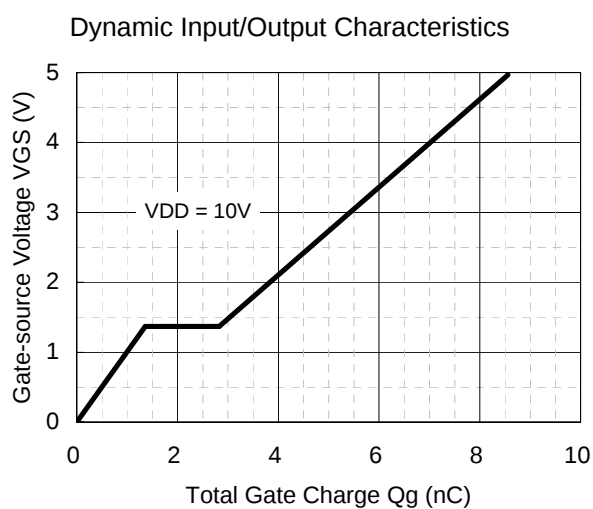
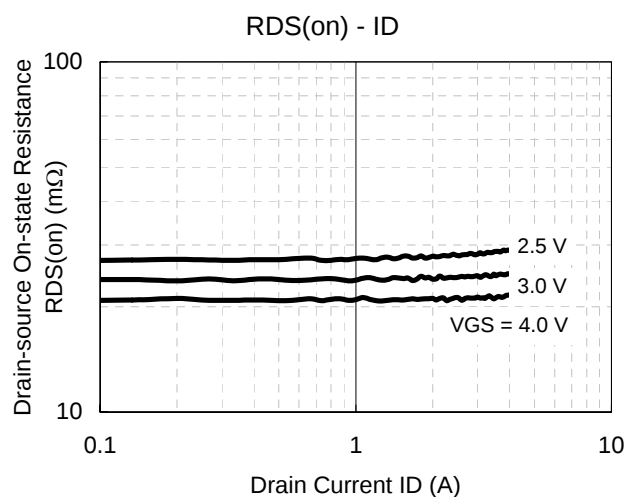
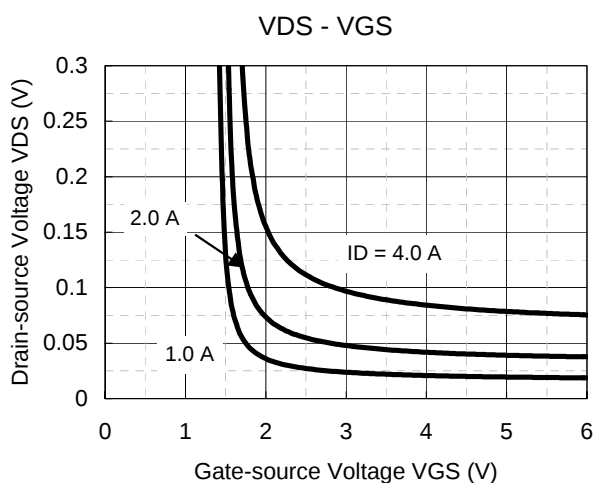
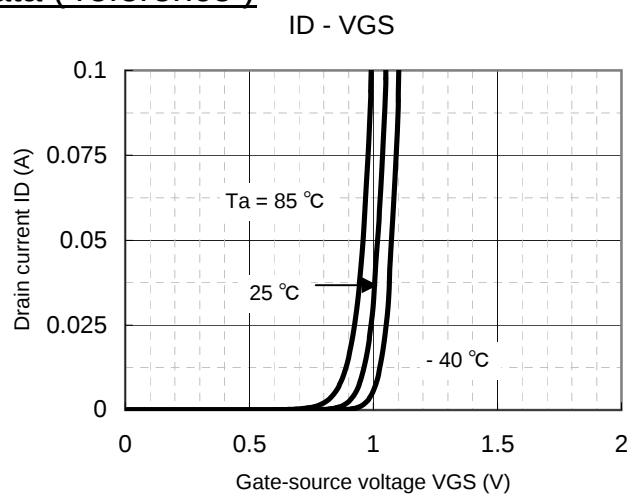
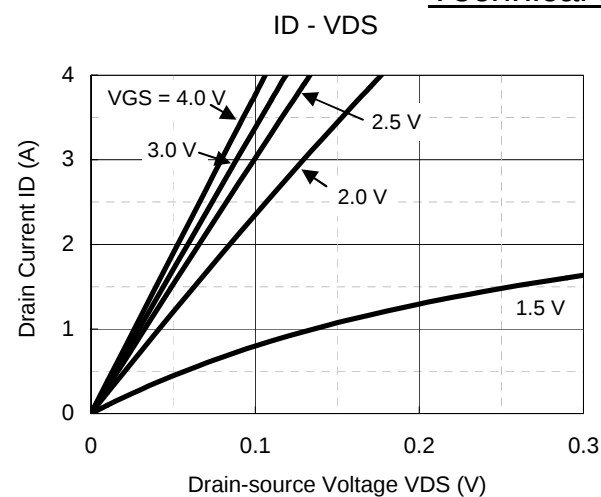
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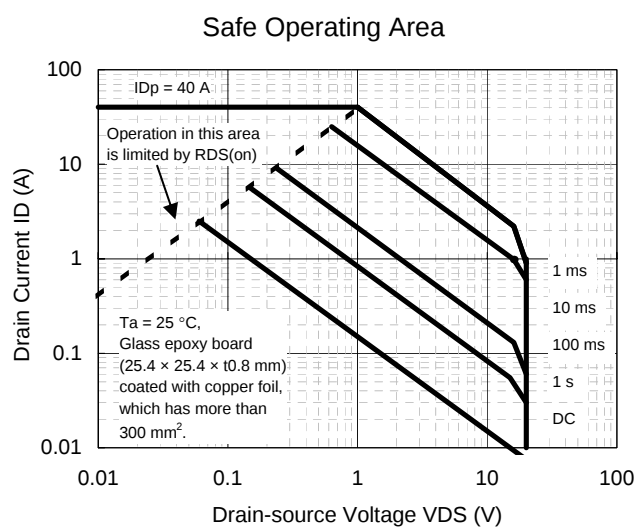
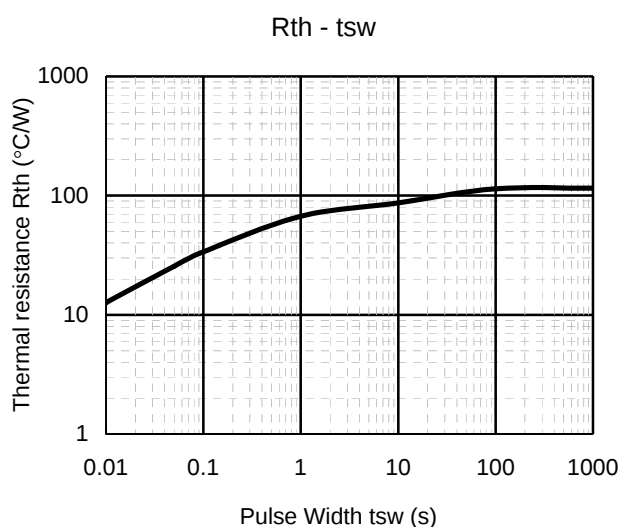
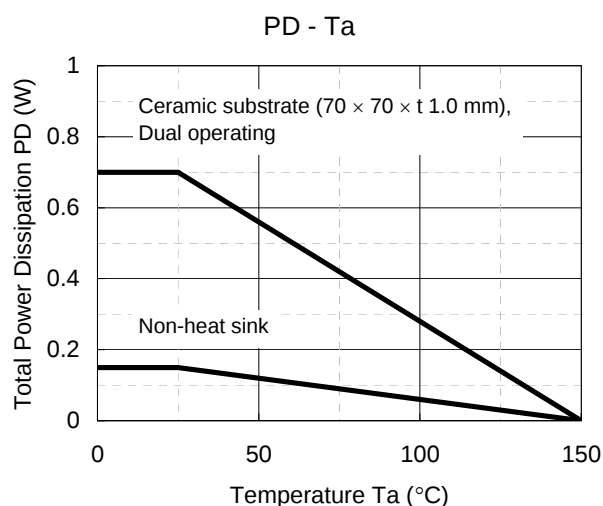
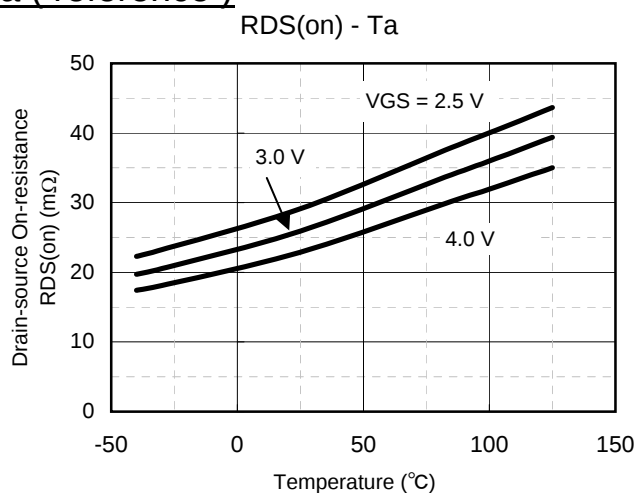
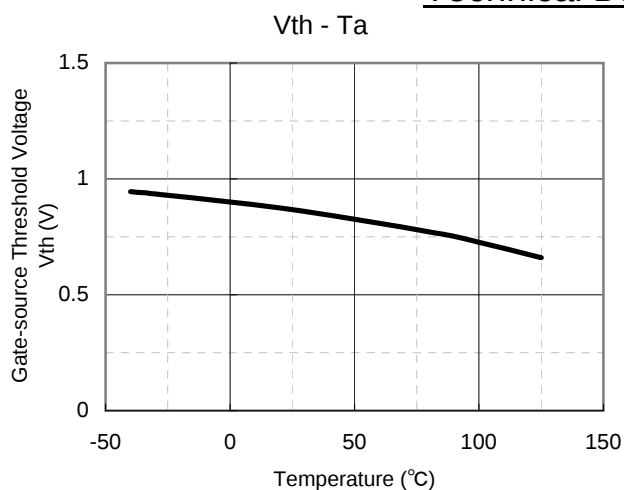
Technical Data (reference)



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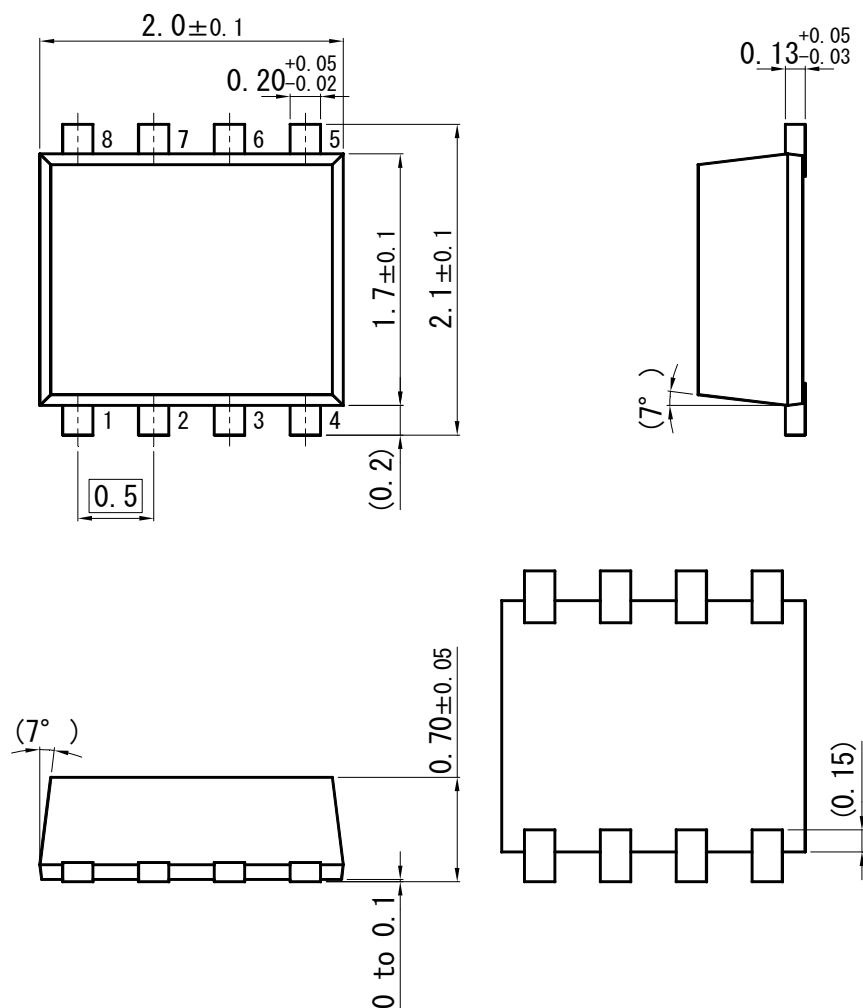


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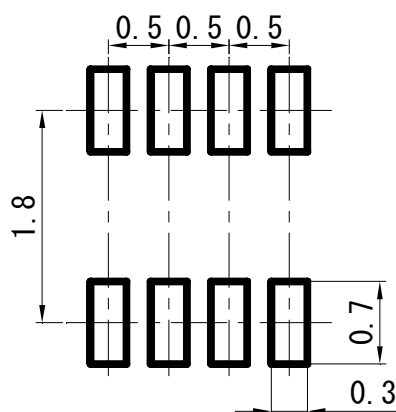
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WSMini8-F1-B

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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